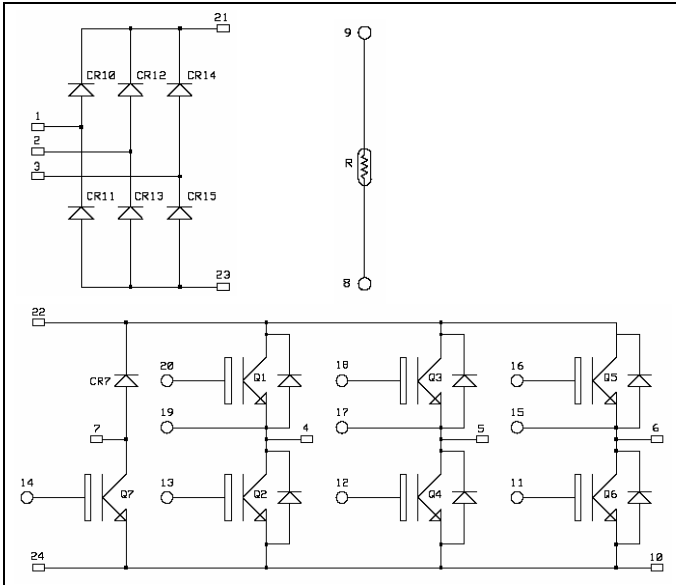
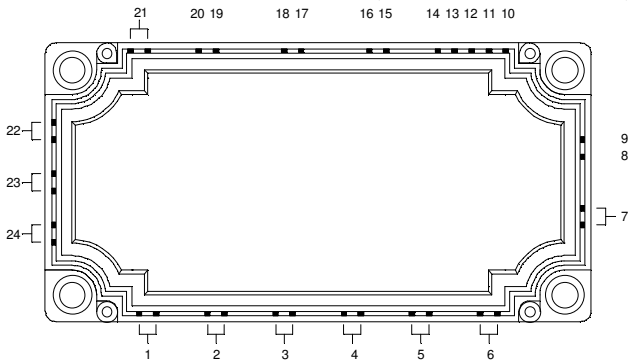


*Input rectifier bridge + Brake
 + 3 Phase Bridge
 Trench IGBT[®] Power Module*

$V_{CES} = 1700V$
 $I_C = 50A @ T_c = 80^{\circ}C$



APTGT50X170RTP3: Without Brake (Pin 7 & 14 not connected)



Application

- AC Motor control

Features

- Trench + Field Stop IGBT[®] Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - Avalanche energy rated
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Low stray inductance
- High level of integration
- Kelvin emitter for easy drive
- Low stray inductance
- Internal thermistor for temperature monitoring

Benefits

- Low conduction losses
- Stable temperature behavior
- Very rugged
- Solderable terminals for easy PCB mounting
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile

All ratings @ $T_j = 25^{\circ}C$ unless otherwise specified

1. Absolute maximum ratings

Diode rectifier Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	1600	V
I_D	DC Forward Current	$T_c = 80^{\circ}C$ 80	A
I_{FSM}	Surge Forward Current	$T_j = 25^{\circ}C$ 500	
		$T_j = 150^{\circ}C$ 400	

 **CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

IGBT & Diode Brake (only for APTGT50X170BTP3) Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V _{CES}	Collector - Emitter Breakdown Voltage	1700	V
I _C	Continuous Collector Current	T _C = 25°C	70
		T _C = 80°C	50
I _{CM}	Pulsed Collector Current	T _C = 25°C	100
V _{GE}	Gate – Emitter Voltage	±20	V
P _D	Maximum Power Dissipation	T _C = 25°C	310
I _F	DC Forward Current	T _C = 80°C	50

IGBT & Diode Inverter Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V _{CES}	Collector - Emitter Breakdown Voltage	1200	V
I _C	Continuous Collector Current	T _C = 25°C	70
		T _C = 80°C	50
I _{CM}	Pulsed Collector Current	T _C = 25°C	100
V _{GE}	Gate – Emitter Voltage	±20	V
P _D	Maximum Power Dissipation	T _C = 25°C	310
RBSOA	Reverse Bias Safe Operating Area	T _j = 125°C	100A @ 1700V
I _F	DC Forward Current	T _C = 80°C	50
I _{FRM}	Repetitive Peak Forward Current	t _p = 1ms	100

2. Electrical Characteristics

Diodes Rectifier Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I _R	Reverse Current	V _R = 1600V T _j = 150°C		3		mA
V _F	Forward Voltage	I _F = 50A T _j = 150°C		1.0		V
R _{thJC}	Junction to Case				0.65	°C/W

IGBT Brake & Diode (only for APTGT50X170BTP3) Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I _{CES}	Zero Gate Voltage Collector Current	V _{GE} = 0V, V _{CE} = 1700V			6	mA
V _{CE(on)}	Collector Emitter on Voltage	V _{GE} = 15V I _C = 50A	T _j = 25°C	2.0	2.4	V
			T _j = 125°C		2.4	
V _{GE(th)}	Gate Threshold Voltage	V _{GE} = V _{CE} , I _C = 2.5mA	5.0	5.8	6.5	V
I _{GES}	Gate – Emitter Leakage Current	V _{GE} = 20V, V _{CE} = 0V			600	nA
C _{ies}	Input Capacitance	V _{GE} = 0V, V _{CE} = 25V f = 1MHz		4400		pF
C _{res}	Reverse Transfer Capacitance			150		
V _F	Forward Voltage	V _{GE} = 0V I _F = 50A	T _j = 25°C	1.8	2.2	V
			T _j = 125°C		1.9	
R _{thJC}	Junction to Case		IGBT		0.4	°C/W
			Diode		0.7	

IGBT & Diode Inverter Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
BV _{CES}	Collector - Emitter Breakdown Voltage	V _{GE} = 0V, I _C = 2.5mA	1700			V
I _{CES}	Zero Gate Voltage Collector Current	V _{GE} = 0V, V _{CE} = 1200V			5	mA
V _{CE(on)}	Collector Emitter on Voltage	V _{GE} = 15V I _C = 50A		2.0 2.4	2.4	V
		T _j = 25°C T _j = 125°C				
V _{GE(th)}	Gate Threshold Voltage	V _{GE} = V _{CE} , I _C = 2.5mA	5.0	5.8	6.5	V
I _{GES}	Gate – Emitter Leakage Current	V _{GE} = 20V, V _{CE} = 0V			600	nA
C _{ies}	Input Capacitance	V _{GE} = 0V ; V _{CE} = 25V		4400		pF
C _{rss}	Reverse Transfer Capacitance	f = 1MHz		150		
T _{d(on)}	Turn-on Delay Time	Inductive Switching (25°C) V _{GE} = ±15V V _{Bus} = 900V I _C = 50A R _G = 22Ω		200		ns
T _r	Rise Time			90		
T _{d(off)}	Turn-off Delay Time			720		
T _f	Fall Time			90		
T _{d(on)}	Turn-on Delay Time	Inductive Switching (125°C) V _{GE} = ±15V V _{Bus} = 900V I _C = 50A R _G = 22Ω		220		ns
T _r	Rise Time			90		
T _{d(off)}	Turn-off Delay Time			820		
T _f	Fall Time			110		
E _{off}	Turn off Energy			22		mJ
V _F	Forward Voltage	V _{GE} = 0V I _F = 50A		1.8 1.9	2.2	V
		T _j = 25°C T _j = 125°C				
Q _{rr}	Reverse Recovery Charge	I _F = 50A V _R = 900V di/dt=990A/μs		19 30		μC
		T _j = 25°C T _j = 125°C				
R _{thJC}	Junction to Case				0.40 0.70	°C/W
		IGBT Diode				

Temperature sensor NTC

Symbol	Characteristic	Min	Typ	Max	Unit
R ₂₅	Resistance @ 25°C		5		kΩ
B _{25/50}	T ₂₅ = 298.16 K		3375		K

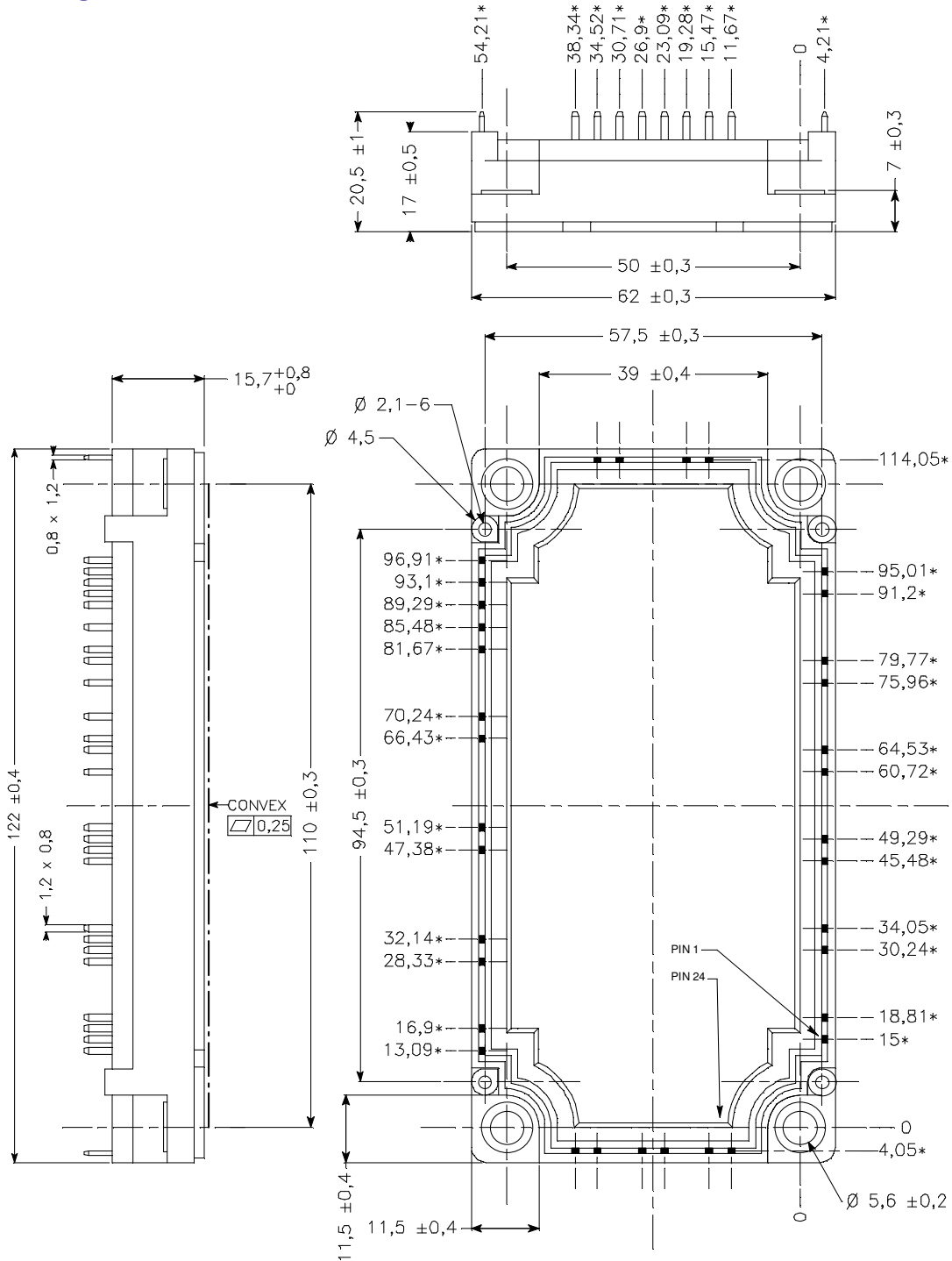
$$R_T = \frac{R_{25}}{\exp \left[B_{25/50} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]}$$

T: Thermistor temperature
R_T: Thermistor value at T

3. Thermal and package characteristics

Symbol	Characteristic	Min	Typ	Max	Unit	
V _{ISOL}	RMS Isolation Voltage, any terminal to case t = 1 min, I _{isol} < 1mA, 50/60Hz	2500			V	
T _J	Operating junction temperature range	-40		150	°C	
T _{STG}	Storage Temperature Range	-40		125		
T _C	Operating Case Temperature	-40		125		
Torque	Mounting torque	To Heatsink	M5		3.3	N.m
Wt	Package Weight				300	g

4. Package outline



ALL DIMENSIONS MARKED " * " ARE TOLERENCED AS : $\oplus_{-0,4}$

APT reserves the right to change, without notice, the specifications and information contained herein

APT's products are covered by one or more of U.S patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. U.S and Foreign patents pending. All Rights Reserved.